

Features

- $V_{DS} = 200V$
- $I_D = 6.0A$
- $R_{DS(ON)} \leq 0.65\Omega @ V_{GS} = 10V$

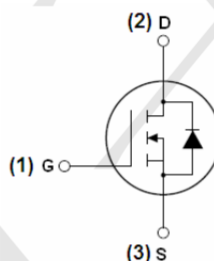
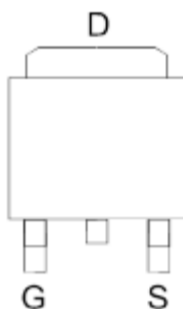
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration

(TO-252-3L)

Top View



Marking:



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	200	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	6.0	A
	$T_C = 100^\circ C$		3.5	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	20	A
Power Dissipation	$T_C = 25^\circ C$	P_D	38.4	W
	Derate above $25^\circ C$		0.31	W/ $^\circ C$
Peak Diode Recovery dv/dt ⁽³⁾		dv/dt	4.5	V/ns
Repetitive Pulse Avalanche Energy ⁽¹⁾		E_{AR}	3.84	mJ
Avalanche current ⁽¹⁾		I_{AR}	5.0	A
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	62.5	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^\circ C$

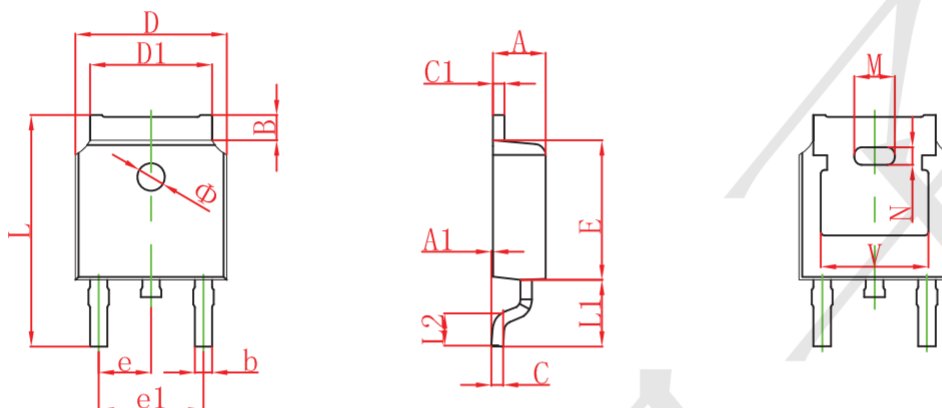
Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	110	$^\circ C/W$
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	3.25	

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu A, V_{GS} = 0V$	200	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	3.0	4.0	
Drain Cut-Off Current	I_{DSS}	$V_{DS} = 160V, V_{GS} = 0V$	-	-	1	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.0A$	-	0.5	0.69	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30V, I_D = 2.5A$	-	2.7	-	S
Dynamic Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 200V, I_D = 7A, V_{GS} = 10V$	-	5.1	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	
Gate-Drain Charge	Q_{gd}		-	2.0	-	
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	182	-	pF
Reverse Transfer Capacitance	C_{rss}		-	5.6	-	
Output Capacitance	C_{oss}		-	46.9	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 100V, I_D = 7A, R_G = 25\Omega$	-	6.3	-	ns
Rise Time	t_r		-	23	-	
Turn-Off Delay Time	$t_{d(off)}$		-	10.7	-	
Fall Time	t_f		-	19.5	-	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I_S		-	6.0	-	A
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 7.0A, V_{GS} = 0V$	-	-	1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 7.0A, di/dt = 100A/\mu s$	-	88	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.25	-	μC

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778 REF.		0.070 REF.	
N	0.762 REF.		0.018 REF.	
L	9.800	10.400	0.386	0.409
L1	2.9 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051